

Complementary Silicon Power Transistors

The MJ15003 and MJ15004 are PowerBase™ power transistors designed for high power audio, disk head positioners and other linear applications.

- High Safe Operating Area (100% Tested) —
250 W @ 50 V
- For Low Distortion Complementary Designs
- High DC Current Gain —
 $h_{FE} = 25$ (Min) @ $I_C = 5$ Adc

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	140	Vdc
Collector–Base Voltage	V_{CBO}	140	Vdc
Emitter–Base Voltage	V_{EBO}	5	Vdc
Collector Current — Continuous	I_C	20	Adc
Base Current — Continuous	I_B	5	Adc
Emitter Current — Continuous	I_E	25	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	250 1.43	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

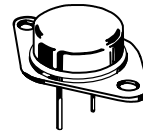
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.70	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes: 1/16" from Case for ≤ 10 seconds	T_L	265	$^\circ\text{C}$

NPN
MJ15003*
PNP
MJ15004*

*ON Semiconductor Preferred Device

20 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
140 VOLTS
250 WATTS



CASE 1-07
TO-204AA
(TO-3)

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

MJ15003 MJ15004

*ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector Emitter Sustaining Voltage (1) ($I_C = 200\text{ mA}$, $I_B = 0$)	$V_{CE(sus)}$	140	—	Vdc
Collector Cutoff Current ($V_{CE} = 140\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 140\text{ Vdc}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	— —	100 2	μAdc mAdc
Collector Cutoff Current ($V_{CE} = 140\text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	250	μAdc
Emitter Cutoff Current ($V_{EB} = 5\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	100	μAdc

SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 50\text{ Vdc}$, $t = 1\text{ s}$ (non repetitive)) ($V_{CE} = 100\text{ Vdc}$, $t = 1\text{ s}$ (non repetitive))	$I_{S/b}$	5 1	— —	Adc
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ON CHARACTERISTICS

DC Current Gain ($I_C = 5\text{ Adc}$, $V_{CE} = 2\text{ Vdc}$)	h_{FE}	25	150	
Collector Emitter Saturation Voltage ($I_C = 5\text{ Adc}$, $I_B = 0.5\text{ Adc}$)	$V_{CE(sat)}$	—	1	Vdc
Base Emitter On Voltage ($I_C = 5\text{ Adc}$, $V_{CE} = 2\text{ Vdc}$)	$V_{BE(on)}$	—	2	Vdc

DYNAMIC CHARACTERISTICS

Current Gain — Bandwidth Product ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 0.5\text{ MHz}$)	f_T	2	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f_{test} = 1\text{ MHz}$)	C_{ob}	—	1000	pF

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

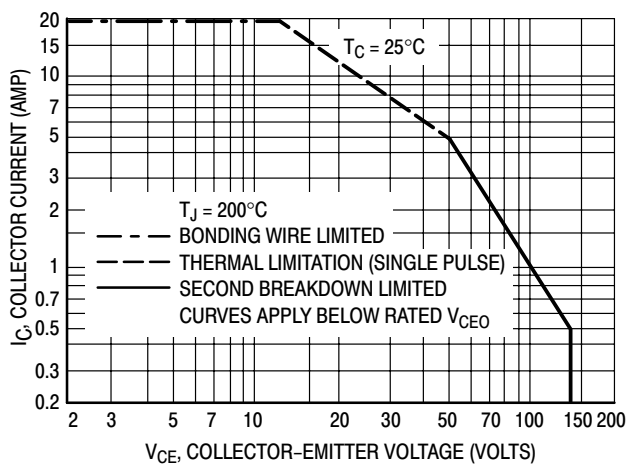


Figure 1. Active-Region Safe Operating Area

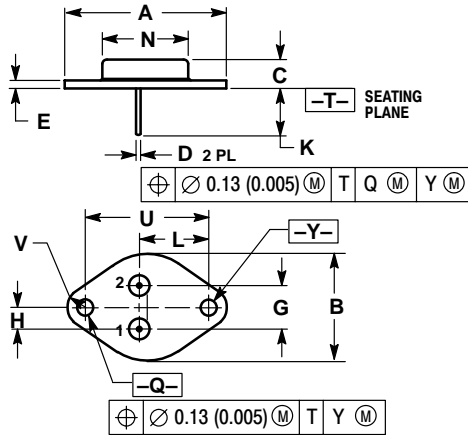
There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)} = 200^\circ\text{C}$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJ15003 MJ15004

PACKAGE DIMENSIONS

CASE 1-07 TO-204AA (TO-3) ISSUE Z




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550	REF	39.37	REF
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430	BSC	10.92	BSC
H	0.215	BSC	5.46	BSC
K	0.440	0.480	11.18	12.19
L	0.665	BSC	16.89	BSC
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187	BSC	30.15	BSC
V	0.131	0.188	3.33	4.77

- STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

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